

FIG. 1

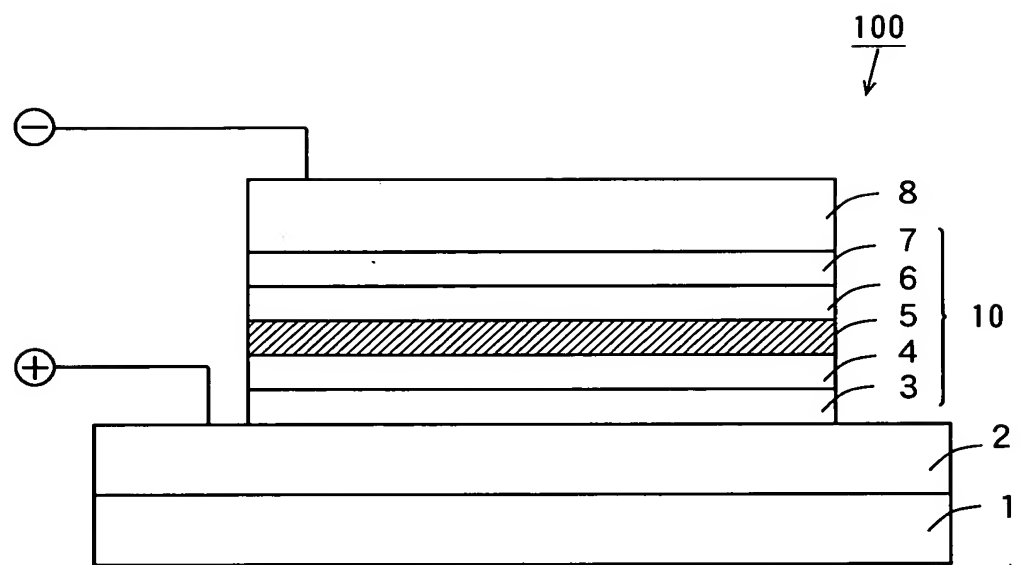


FIG. 2

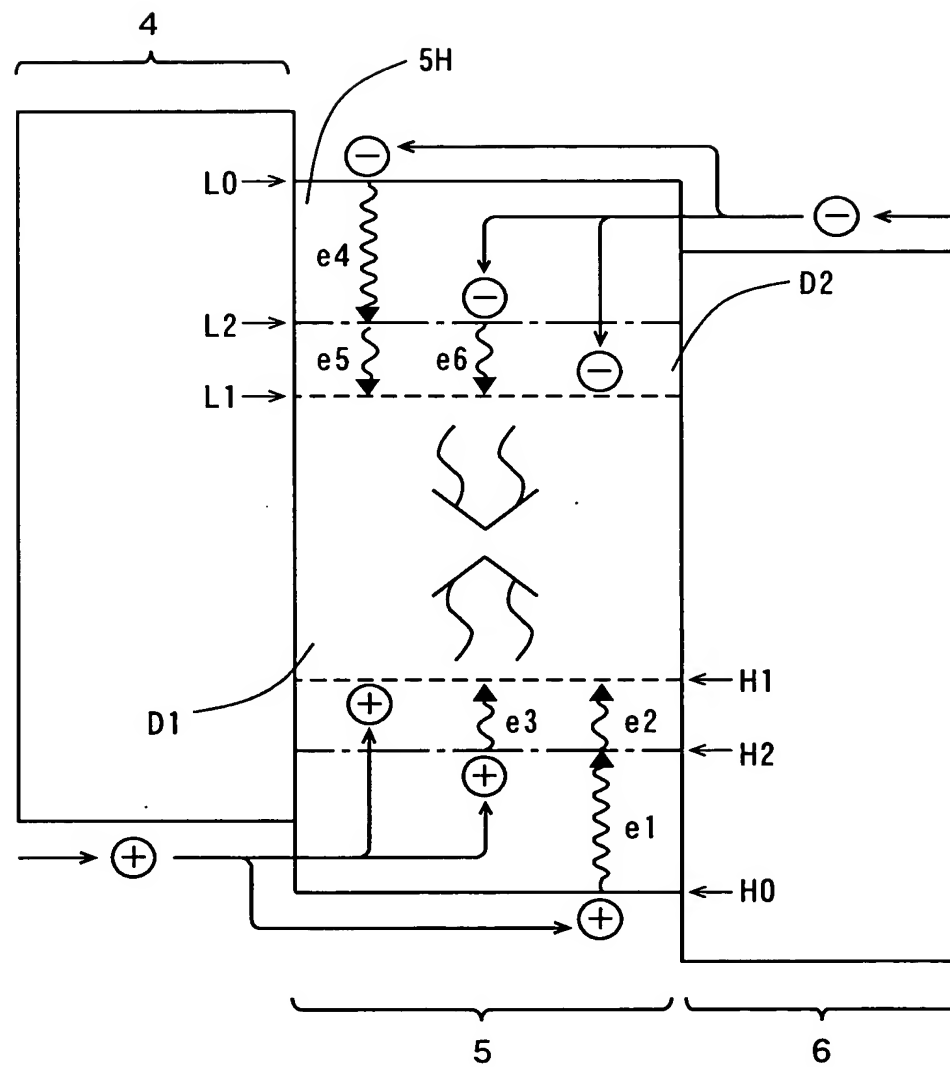
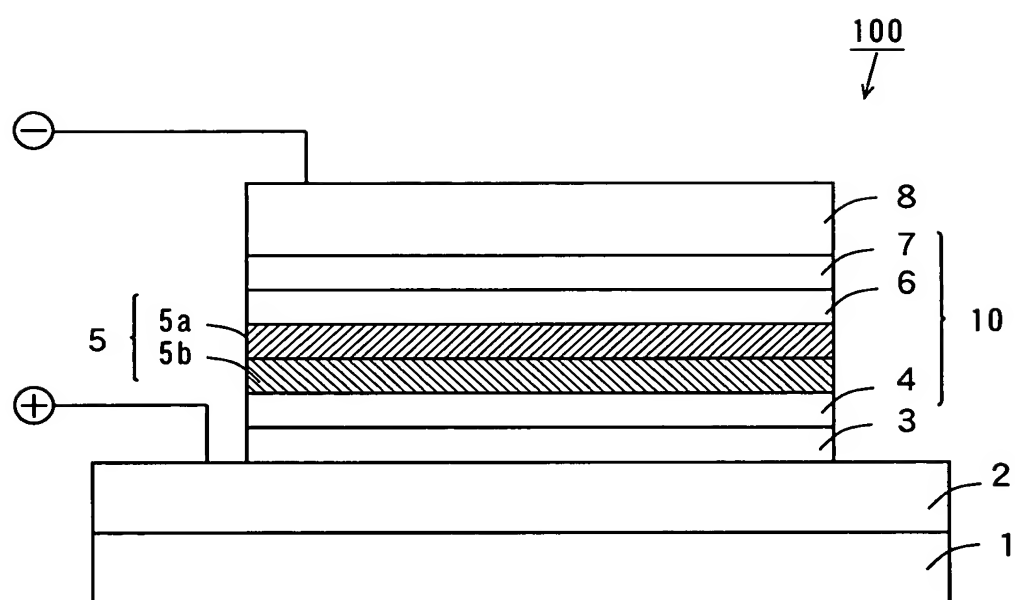
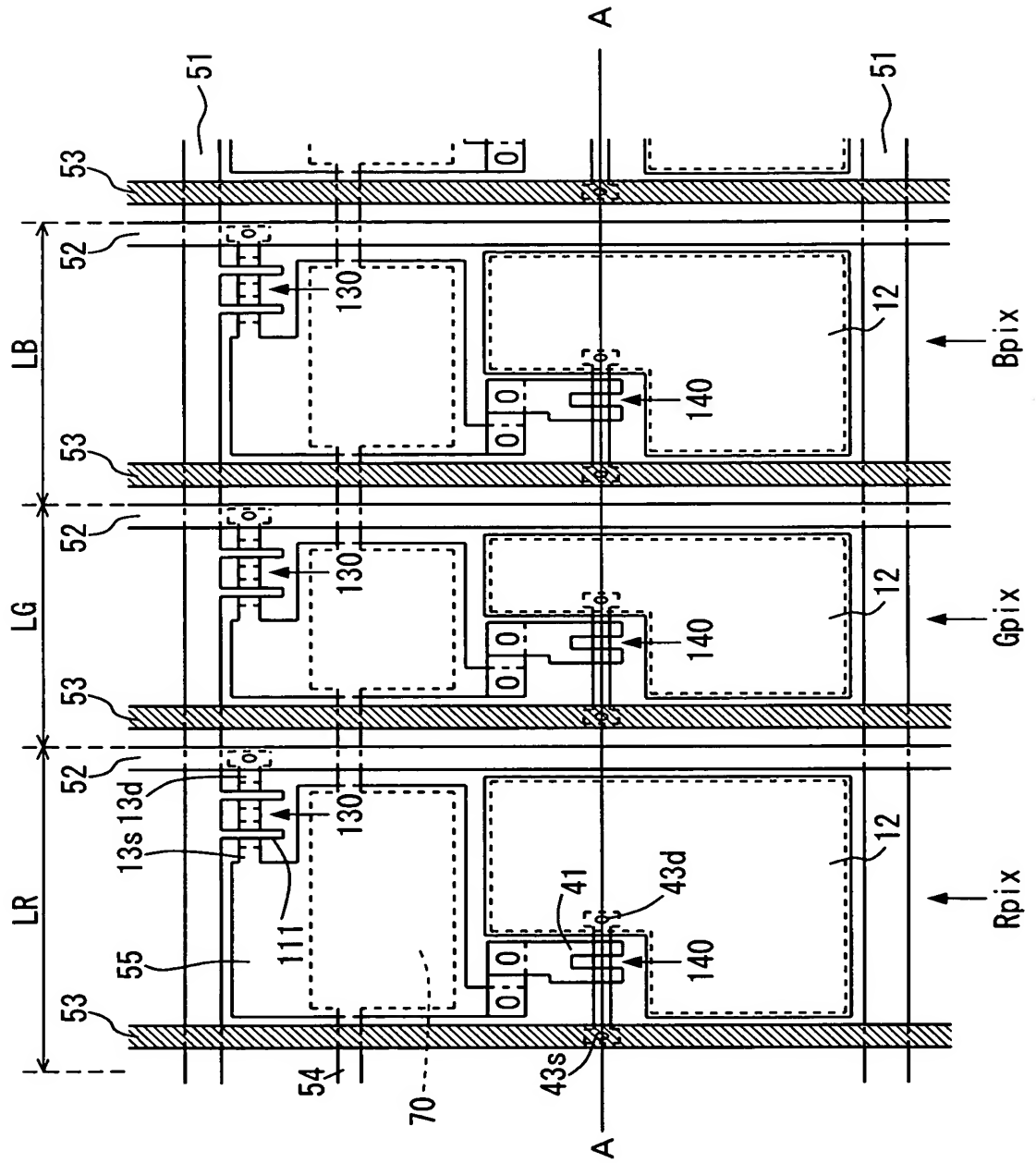


FIG. 3





This diagram shows a cross-sectional view of a multi-layered semiconductor device, likely a color filter or sensor array. The device consists of several stacked layers: a top substrate (10), a middle layer (11), a buffer layer (13), a conductive layer (15), a dielectric layer (12), and a bottom substrate (18). The device is divided into three vertical sections, each corresponding to a different input region: Bpix (Blue pixel), Gpix (Green pixel), and Rpix (Red pixel). Each section contains a series of conductive lines (22, 24, 26, 28, 30, 32) that are patterned to form a pixel structure. The Bpix section shows a series of conductive lines (22, 24, 26, 28, 30, 32) that are patterned to form a pixel structure. The Gpix section shows a series of conductive lines (22, 24, 26, 28, 30, 32) that are patterned to form a pixel structure. The Rpix section shows a series of conductive lines (22, 24, 26, 28, 30, 32) that are patterned to form a pixel structure. The device also includes a series of conductive lines (140, 141, 143s, 143d, 144) that are patterned to form a pixel structure. The device is shown in a cross-sectional view, with the layers and conductive lines clearly visible.

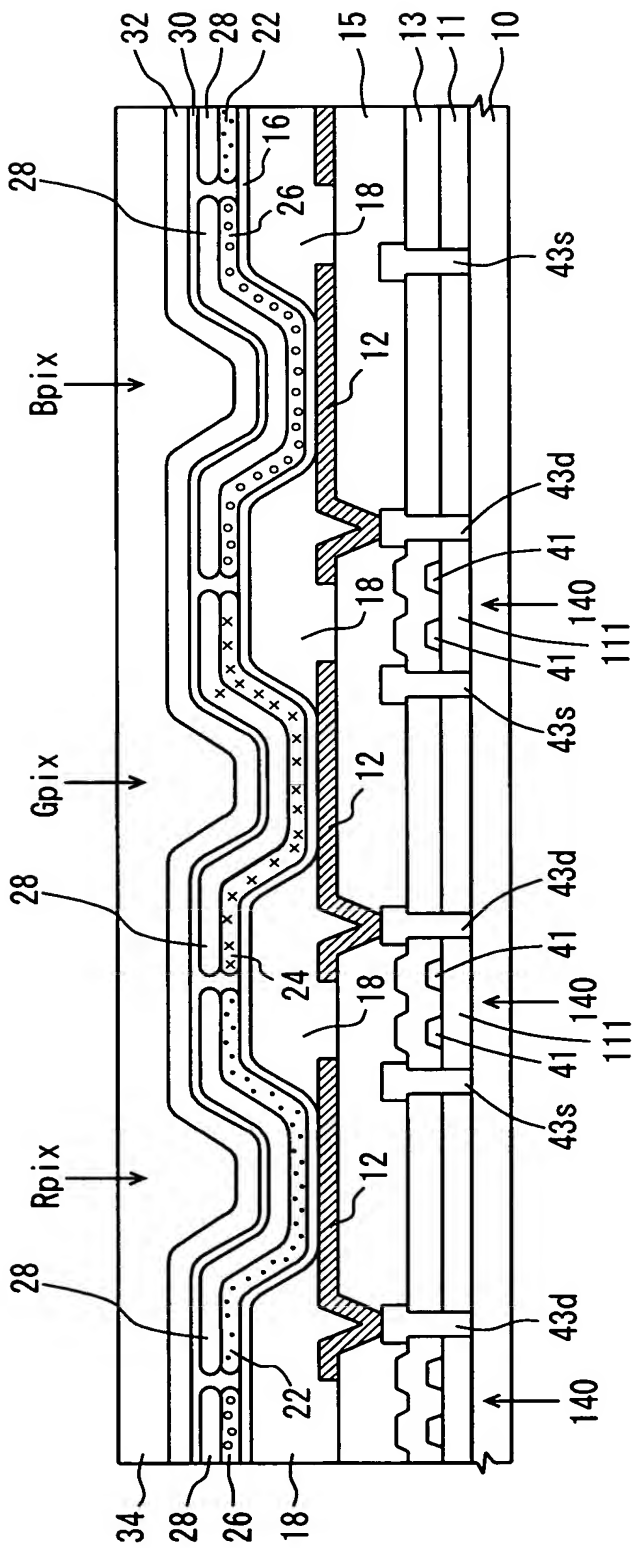


FIG. 6

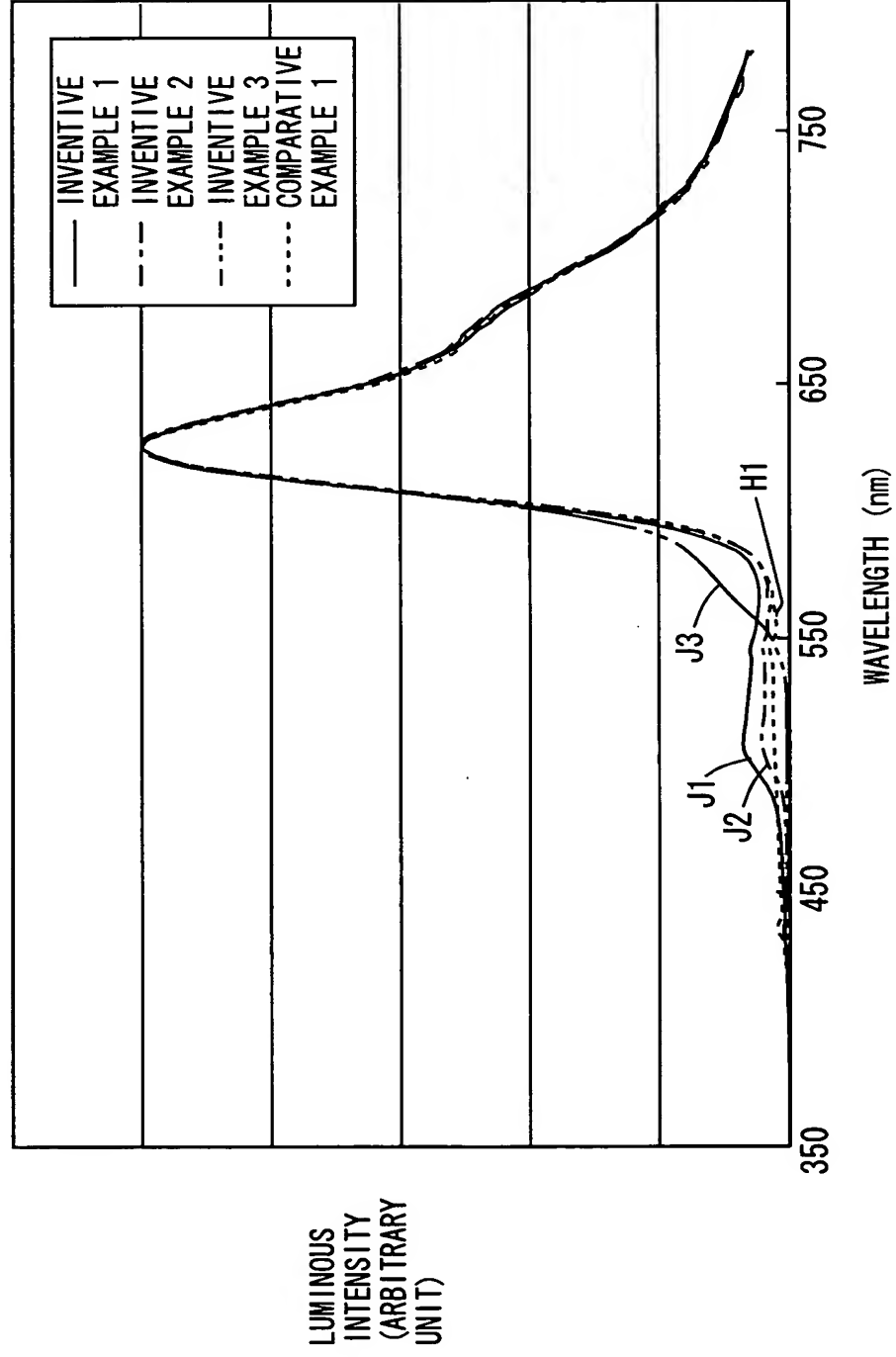


FIG. 7

